ST(意法) TN1205H-6G-TR PDF

深圳创难电子有限公司

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High temperature 12 A SCRs

Datasheet - production data

Features

- High junction temperature: T_i = 150 °C
- Medium current SCRs
- High noise immunity up to 150 °C
- RoHS (2002/95/EC) compliant
- 600 V V_{DRM}, V_{RRM}

Application

- General purpose AC line load switching
- Motor control circuits
- Small home appliances
- Lighting
- Inrush current limiting circuits
- Over-voltage crowbar protection

Description

Available in standard gate triggering levels, the TN1205H SCR series has very high switching capability up to junction temperature of 150 °C.

These products fit all modes of control found in applications such as overvoltage crowbar protection, motor control circuits in power tools and kitchen aids, inrush current limiting circuits, capacitive discharge ignition and voltage regulation circuits.

These products are particulary adapted for use in areas where the ambient temperature is high or the ventilation low, or where an increase of power density is required.

Through-hole or surface-mount packages provide performance in a limited space area.

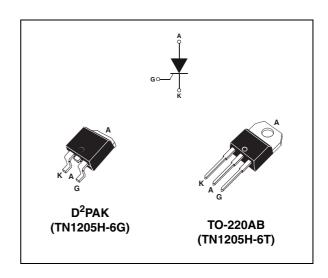


Table 1. Device summary

Order code	Package	V _{DRM} , V _{RRM}	I _{GT}	
TN1205H-6T	TO-220AB	600 V	2 to 5 mA	
TN1205H-6G	D ² PAK	000 V	2 to 3 IIIA	

Characteristics TN1205H

1 Characteristics

 Table 2.
 Absolute ratings (limiting values)

Symbol	Parameter			Value	Unit
I _{T(RMS)}	On-state rms current (180° conduction angle)	TO220-AB, T 126 °C		12	Α
I _{T(AV)}	Average on-state current (180° conduction angle)	D^2 PAK $T_c = 136 ^{\circ}$ C		7.6	Α
	Non repetitive aurea peak on state aureant	$t_{p} = 8.3 \text{ ms}$	T _ 25 °C	126	Α
I _{TSM}	Non repetitive surge peak on-state current	$t_p = 10 \text{ ms}$	T _j = 25 °C	120	
l ² t	I^2 t Value for fusing $t_p = 10 \text{ ms}$				A ² S
V_{DSM} , V_{RSM}	Non repetitive surge peak off-state voltage $t_p =$		t _p = 10 ms	V _{DRM} , V _{RRM} +100	V
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $I_{CT} = 100 \text{ ns}$		T _j = 150 °C	100	A/µs
I _{GM}	Peak gate current $t_p = 20 \mu s$		T _j = 150 °C	4	Α
P _{G(AV)}	Average gate power dissipation $T_j = 150 ^{\circ}\text{C}$				W
V_{RGM}	Maximum peak reverse gate voltage			5	V
T _{stg} T _j	Storage junction temperature range Operating junction temperature range			- 40 to + 150	°C
T _L	Maximum lead temperature for soldering during 10 s.			260	°C

Table 3. Electrical characteristics ($T_j = 25$ °C, unless otherwise specified)

Symbol	Test conditions			Value	Unit
	V 40 V D 20 O			2	mΛ
I_{GT} $V_D = 12 \text{ V}, R_L = 33 \Omega$		MAX.	5	mA	
V _{GT}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$		MAX.	1.3	٧
V _{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$ MIN.		MIN.	0.2	V
I _H	I _T = 500 mA gate open MAX		MAX.	20	mA
ΙL	I _G = 1.2 I _{GT}		MAX.	40	mA
dV/dt	V = 679/ V gata apan	T _j = 125 °C	MIN.	200	V/µs
u v/ut	V _D = 67% V _{DRM} gate open	T _j = 150 °C	IVIIIN.	100	ν/μ5
t _{gt}	$I_{TM} = 40 \text{ A}, V_D = 500 \text{ V}, I_G = 100 \text{ mA}, dI_G/dt = 5 \text{ A/}\mu\text{s}$		typ.	1.9	μs
t _q	$ \begin{array}{c} V_{DM} = 335 \text{ V, Tj} = 125 \text{ °C, } I_{TM} = 20 \text{ A, } V_{R} = 25 \text{ V, } (dI_{T}/dt)_{Max} = 30 \text{ A/}\mu\text{s,} \\ dV_{D}/dt = 50 \text{ V/}\mu\text{s, } R_{GK} = 100 \Omega \end{array} $		typ.	65	μs

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Table 4. Static characteristics

Symbol	Test conditions			Value	Unit
V _T	$I_{TM} = 24 \text{ A}, t_p = 380 \ \mu \text{s}$	T _j = 25 °C		1.6	V
V_{TD}	Threshold voltage	T _j = 150 °C		0.8	V
R_d	Dynamic resistance	T _j = 150 °C	MAX.	30	mΩ
		T _j = 25 °C	IVIAA.	5	μΑ
I _{DRM} I _{RRM}		T _j = 125 °C		1	- mA
		T _j = 150 °C		3	

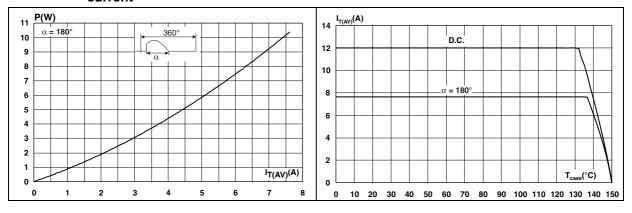
Table 5. Thermal resistance

Symbol	Parameter			Value Max.	Unit
R _{th(j-c)}	Junction to case (DC)			1.3	°C/W
D. Lunction to ambient (DC)	Junction to ambient (DC)	$S^{(1)} = 1 \text{ cm}^2$	D ² PAK	45	°C/W
R _{th(j-a)}	odificion to ambient (DC)		TO-220AB	60	C/VV

^{1.} S = Copper surface under tab

Figure 1. Maximum average power dissipation vs. average on-state current

Figure 2. Average and DC on-state current vs. case temperature



Characteristics TN1205H

Figure 3. Average and DC on-state current vs. ambient temperature

Figure 4. Relative variation of thermal impedance vs. pulse duration

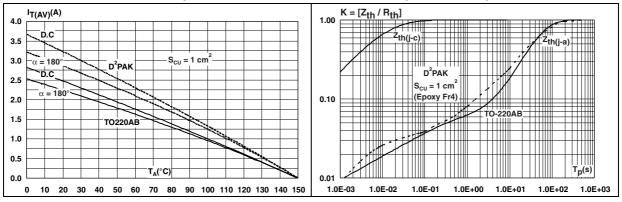


Figure 5. Relative variation of I_{GT}, V_{GT}, I_H, I_L vs. junction temperature (typical values)

Figure 6. Relative variation of static dV/dt immunity vs. junction temperature (typical values)

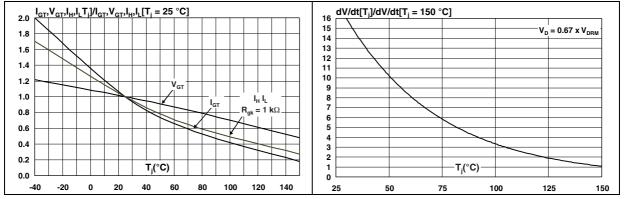
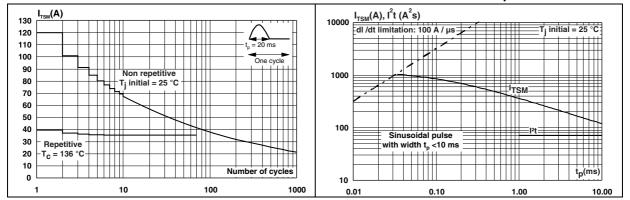


Figure 7. Surge peak on-state current vs. number of cycles

Figure 8. Non repetitive surge peak on-state current and corresponding value of I²t vs. sinusoidal pulse width



TN1205H Characteristics

Figure 9. On-state characteristics (maximum values)

Figure 10. Relative variation of leakage current vs. junction temperature for different values of blocking voltage

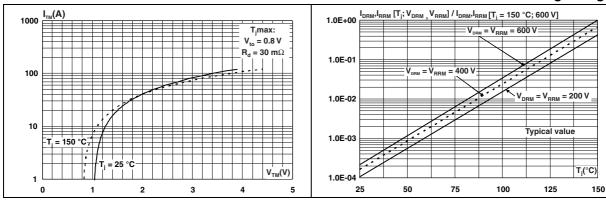
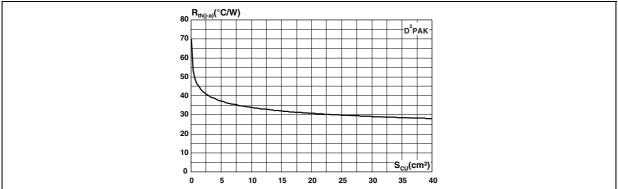
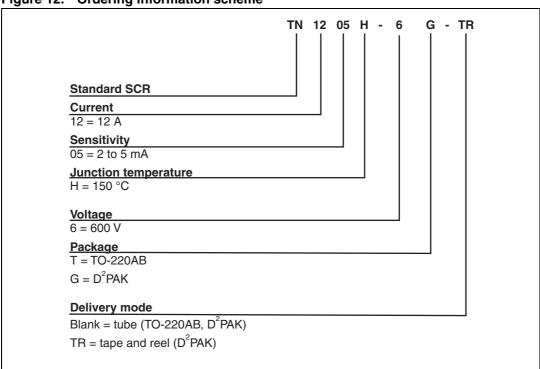


Figure 11. Thermal resistance junction to ambient vs. copper surface under tab (D²PAK, printed circuit board FR4, copper thickness: 35 μm)



2 Ordering information scheme

Figure 12. Ordering information scheme



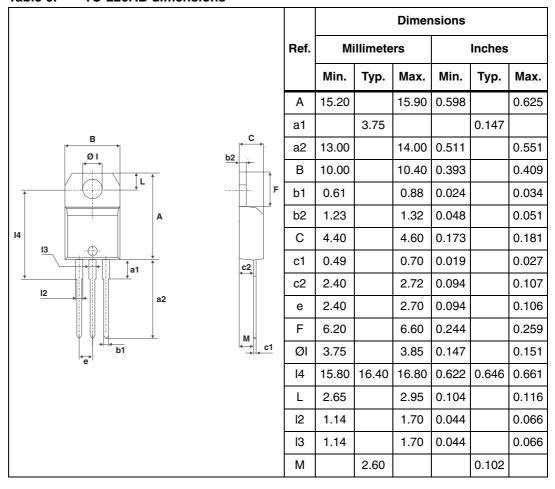
TN1205H Package information

3 Package information

- Epoxy meets UL94, V0
- Lead-free package

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 6. TO-220AB dimensions



Package information TN1205H

Table 7. D²PAK Dimensions

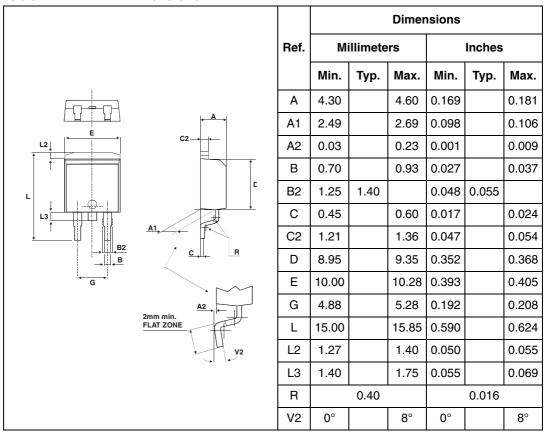
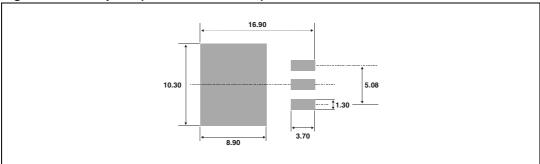


Figure 13. Footprint (dimensions in mm)



4 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
TN1205H-6T	TN1205H6T	TO-220AB	2.0 g	50	Tube
TN1205H-6G	TN1205H6G	D ² PAK	1.5 g	50	Tube
TN1205H-6G-TR	TN1205H6G	D ² PAK	1.5 g	1000	Tape and reel

5 Revision history

Table 9. Document revision history

Date	Revision	Changes	
17-Feb-2011	1	First issue.	
26-Sep-2011	2	Corrected typographical error in Features and Description.	
17-Jan-2012	3	Updated units for t _{gt} in <i>Table 3</i> .	
26-Apr-2012	4	Moved junction temperature to top of features list. Description reworded for readability. No technical changes.	

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